Description

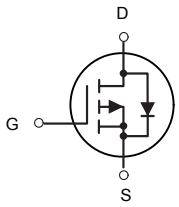
The IRF7404PBF uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

SOP-8

General Features

V_{DS} = -20V I_D = -20A

$R_{DS(ON)}$ < 19mΩ@ V_{GS}=10V



P-Channel MOSFET

Application

Battery protection

Load switch

Uninterruptible power supply

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
IRF7404PBF	SOP-8	F7404 XXXX	3000

Absolute Maximum Ratings (Tc=25℃ unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-20	V
V_{GS}	Gate-Source Voltage	±12	V
I_D@T_A=25℃	Drain Current[3], V_{GS} @ 10V	-20	A
I_D@T_A=70℃	Drain Current[3], V_{GS} @ 10V	-16	A
I_{DM}	Pulsed Drain Current[1]	-68	A
P_D@T_A=25℃	Total Power Dissipation	18	W
T_{STG}	Storage Temperature Range	-55 to 150	℃
T_J	Operating Junction Temperature Range	-55 to 150	℃
Rthj-a	Maximum Thermal Resistance, Junction-ambient[3]	75	℃/W

Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=-250uA	-20	---	---	V
$\triangle BV_{DSS}/\triangle T_J$	BV_{DSS} Temperature Coefficient	Reference to 25℃ , I_D=-1mA	---	-0.012	---	V/℃
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=-4.5V , I_D=-10A	---	15	19	mΩ
		V_{GS}=-2.5V , I_D=-8A	---	19	23	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =-250uA	-0.4	-0.7	-1.0	V
$\triangle V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	2.94	---	mV/℃
I_{DSS}	Drain-Source Leakage Current	V_{DS}=-15V , V_{GS}=0V , T_J=25℃	---	---	1	uA
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±12 V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=-5V , I_D=-10A	---	43	---	S
Q_g	Total Gate Charge (-4.5V)	V_{DS}=-10V , V_{GS}=-4.5V , I_D=-10A	---	35	---	nC
Q_{gs}	Gate-Source Charge		---	5.0	---	
Q_{gd}	Gate-Drain Charge		---	10	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DD}=-10V , V_{GS}=-4.5V , R_G=3.3Ω, I_D=-10A	---	12.0	---	ns
T_r	Rise Time		---	40.0	---	
$T_{d(off)}$	Turn-Off Delay Time		---	30	---	
T_f	Fall Time		---	10	---	
C_{iss}	Input Capacitance	V_{DS}=-15V , V_{GS}=0V , f=1MHz	---	2800	---	pF
C_{oss}	Output Capacitance		---	690	---	
C_{rss}	Reverse Transfer Capacitance		---	590	---	
I_S	Continuous Source Current[1,4]	V_G=V_D=0V , Force Current	---	---	-20.0	A
I_{SM}	Pulsed Source Current[2,4]		---	---	---	A
V_{SD}	Diode Forward Voltage[2]	V_{GS}=0V , I_S=-1A , T_J=25℃	---	---	-1.2	V
t_{rr}	Reverse Recovery Time	IF=-10A , dI/dt=100A/μs , T_J =25℃	---	27	---	nS
Q_{rr}	Reverse Recovery Charge		---	17.8	---	nC

Note :
1.The data tested by surface mounted on a 1 inch^2 FR-4 board with 2OZ copper.
2.The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%
3.The power dissipation is limited by 150℃ junction temperature
4.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics

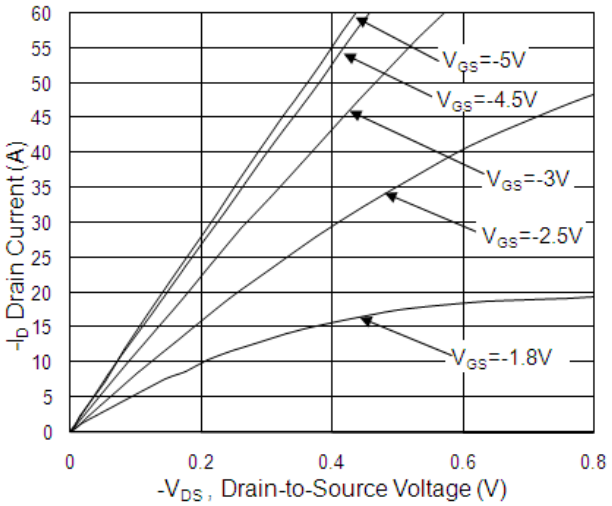


Fig.1 Typical Output Characteristics

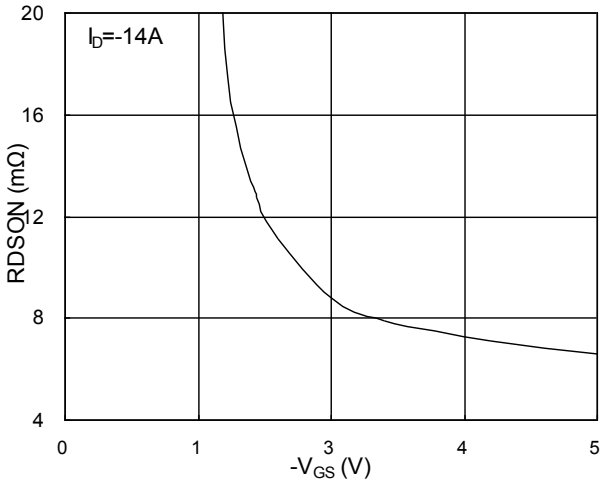


Fig.2 On-Resistance vs. G-S Voltage

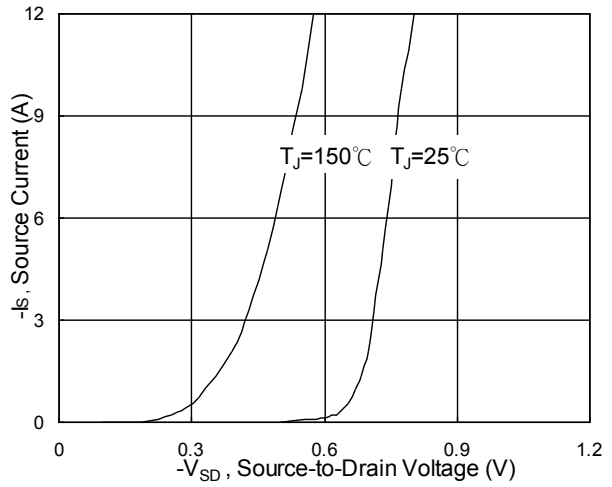


Fig.3 Forward Characteristics of Reverse

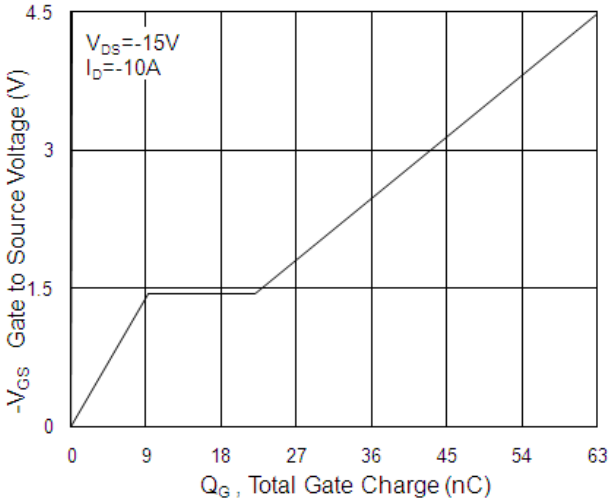


Fig.4 Gate-charge Characteristics

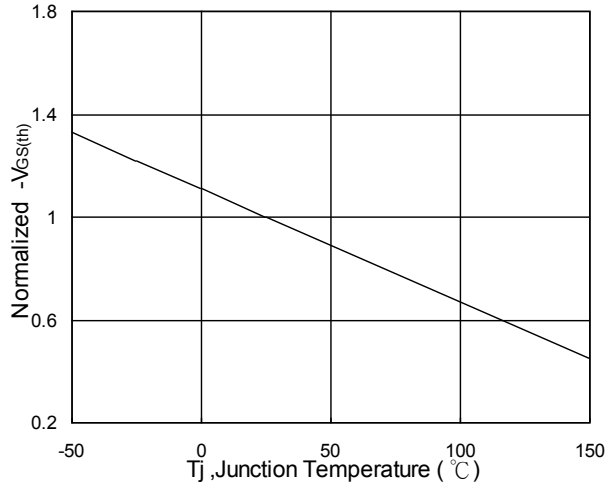


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

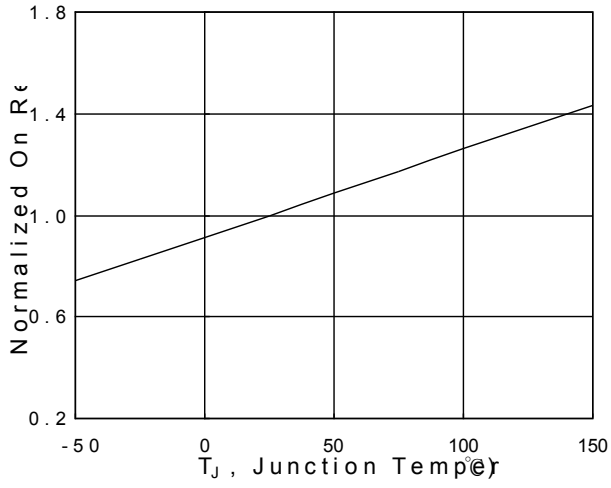


Fig.6 Normalized R_{DSON} vs. T_J

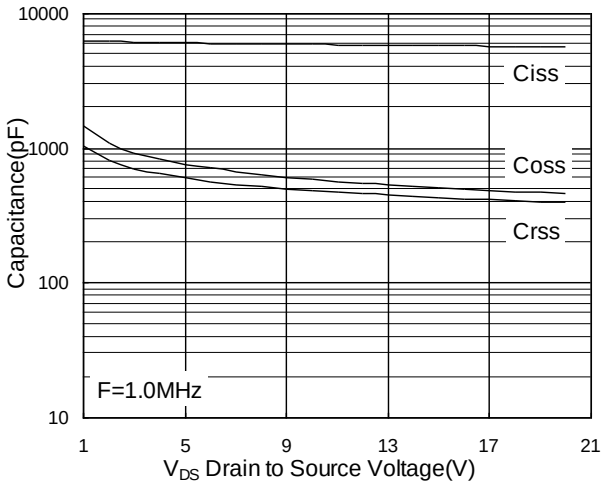


Fig.7 Capacitance

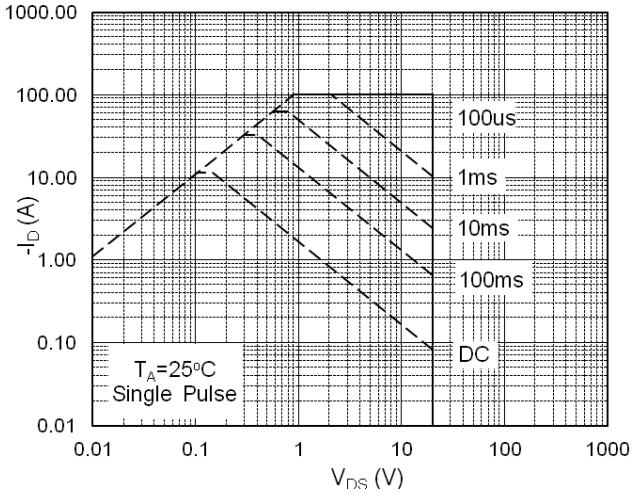


Fig.8 Safe Operating Area

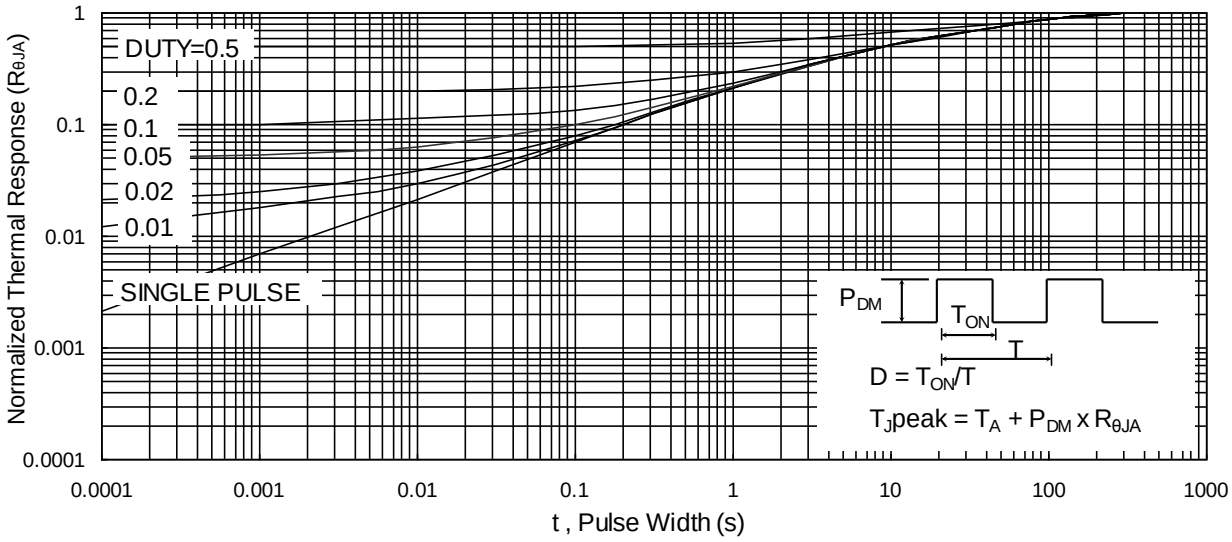


Fig.9 Normalized Maximum Transient Thermal Impedance

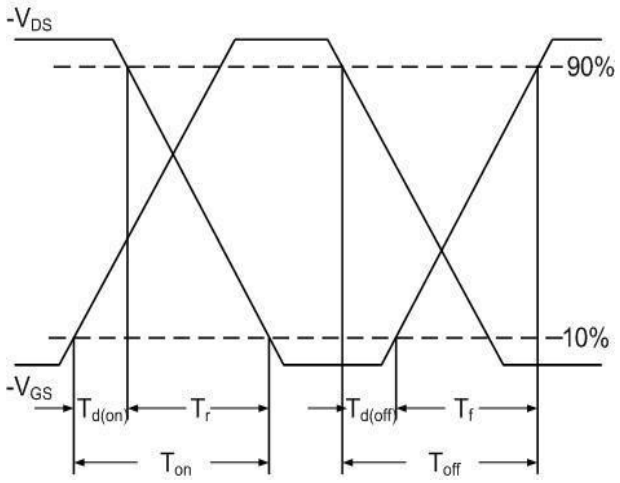


Fig.10 Switching Time Waveform

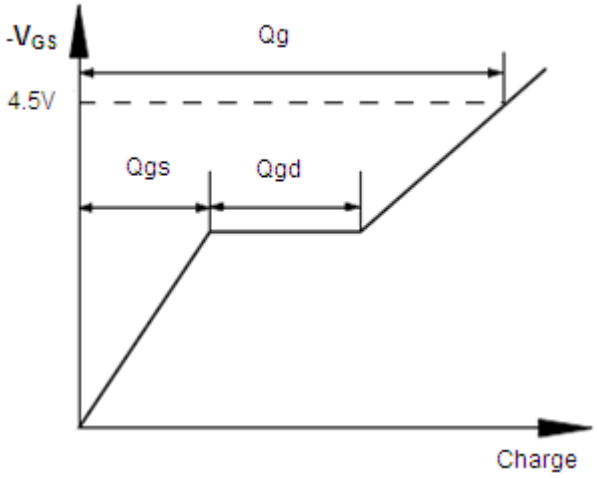
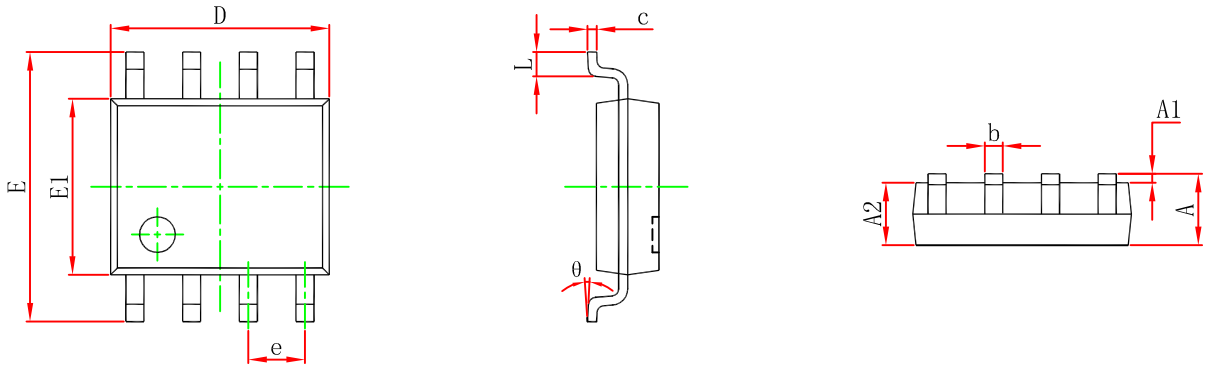
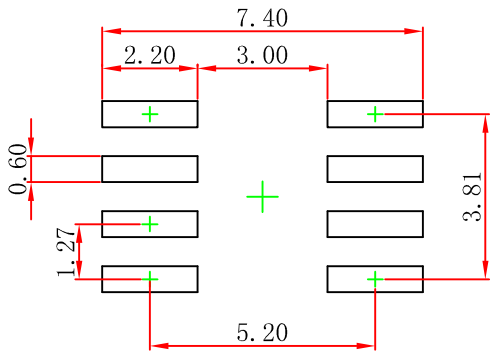


Fig.11 Gate Charge Waveform

SOP-8 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	**Max**	**Min**	**Max**
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.007	0.010
D	4.800	5.000	0.189	0.197
e	1.270 (BSC)		0.050 (BSC)	
E	5.800	6.200	0.228	0.244
E1	3.800	4.000	0.150	0.157
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°



Note:
1.Controlling dimension:in millimeters.
2.General tolerance:± 0.05mm.
3.The pad layout is for reference purposes only.

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